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Kind regards,

Team Nexperia

# DATA SHEET

## **PDTC144W series**

NPN resistor-equipped transistors;

$R1 = 47\text{ k}\Omega$ ,  $R2 = 22\text{ k}\Omega$

Product data sheet  
Supersedes data of 2004 Mar 23

2004 Aug 17

# NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$

## PDTC144W series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

| SYMBOL           | PARAMETER                 | TYP. | MAX. | UNIT       |
|------------------|---------------------------|------|------|------------|
| V <sub>CEO</sub> | collector-emitter voltage | –    | 50   | V          |
| I <sub>O</sub>   | output current (DC)       | –    | 100  | mA         |
| R1               | bias resistor             | 47   | –    | k $\Omega$ |
| R2               | bias resistor             | 22   | –    | k $\Omega$ |

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

| TYPE NUMBER | PACKAGE       |        | MARKING CODE       | PNP COMPLEMENT |
|-------------|---------------|--------|--------------------|----------------|
|             | PHILIPS       | EIAJ   |                    |                |
| PDTC144WE   | SOT416        | SC-75  | 42                 | PDTA144WE      |
| PDTC144WEF  | SOT490        | SC-89  | 34                 | PDTA144WEF     |
| PDTC144WK   | SOT346        | SC-59  | 41                 | PDTA144WK      |
| PDTC144WM   | SOT883        | SC-101 | DD                 | PDTA144WM      |
| PDTC144WS   | SOT54 (TO-92) | SC-43  | TC144W             | PDTA144WS      |
| PDTC144WT   | SOT23         | –      | *20 <sup>(1)</sup> | PDTA144WT      |
| PDTC144WU   | SOT323        | SC-70  | *20 <sup>(1)</sup> | PDTA144WU      |

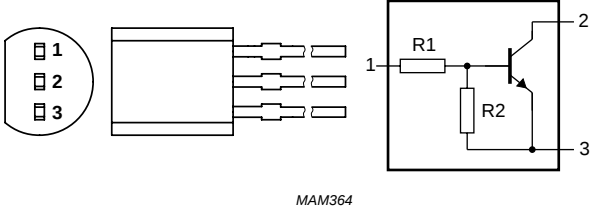
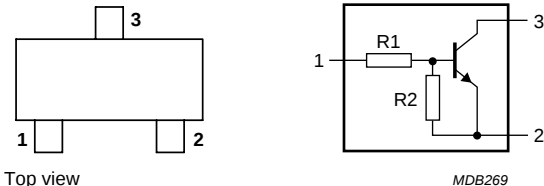
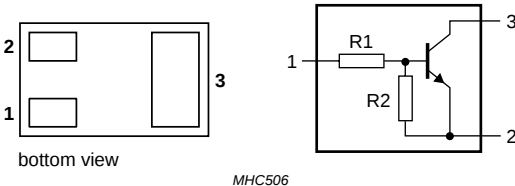
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 22 kΩ

PDTC144W series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

| TYPE NUMBER                                                    | SIMPLIFIED OUTLINE AND SYMBOL                                                                                 | PINNING     |                              |
|----------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------|-------------|------------------------------|
|                                                                |                                                                                                               | PIN         | DESCRIPTION                  |
| PDTC144WS                                                      | <br>MAM364                  | 1<br>2<br>3 | base<br>collector<br>emitter |
| PDTC144WE<br>PDTC144WEF<br>PDTC144WK<br>PDTC144WT<br>PDTC144WU | <br>Top view<br>MDB269     | 1<br>2<br>3 | base<br>emitter<br>collector |
| PDTC144WM                                                      | <br>bottom view<br>MHC506 | 1<br>2<br>3 | base<br>emitter<br>collector |

NPN resistor-equipped transistors;  
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PDTC144W series

## ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |                                                                                  |         |
|-------------|---------|----------------------------------------------------------------------------------|---------|
|             | NAME    | DESCRIPTION                                                                      | VERSION |
| PDTC144WE   | –       | plastic surface mounted package; 3 leads                                         | SOT416  |
| PDTC144WEF  | –       | plastic surface mounted package; 3 leads                                         | SOT490  |
| PDTC144WK   | –       | plastic surface mounted package; 3 leads                                         | SOT346  |
| PDTC144WM   | –       | leadless ultra small plastic package; 3 solder lands; body<br>1.0 × 0.6 × 0.5 mm | SOT883  |
| PDTC144WS   | –       | plastic single-ended leaded (through hole) package; 3 leads                      | SOT54   |
| PDTC144WT   | –       | plastic surface mounted package; 3 leads                                         | SOT23   |
| PDTC144WU   | –       | plastic surface mounted package; 3 leads                                         | SOT323  |

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS               | MIN. | MAX. | UNIT |
|------------------|-------------------------------|--------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter             | –    | 50   | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                | –    | 50   | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector           | –    | 10   | V    |
| V <sub>i</sub>   | input voltage                 |                          |      |      |      |
|                  | positive                      |                          | –    | +40  | V    |
|                  | negative                      |                          | –    | –10  | V    |
| I <sub>O</sub>   | output current (DC)           |                          | –    | 100  | mA   |
| I <sub>CM</sub>  | peak collector current        |                          | –    | 100  | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C |      |      |      |
|                  | SOT54                         | note 1                   | –    | 500  | mW   |
|                  | SOT23                         | note 1                   | –    | 250  | mW   |
|                  | SOT346                        | note 1                   | –    | 250  | mW   |
|                  | SOT323                        | note 1                   | –    | 200  | mW   |
|                  | SOT490                        | notes 1 and 2            | –    | 250  | mW   |
|                  | SOT883                        | notes 2 and 3            | –    | 250  | mW   |
|                  | SOT416                        | note 1                   | –    | 150  | mW   |
| T <sub>stg</sub> | storage temperature           |                          | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                          | –    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                          | –65  | +150 | °C   |

## Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

NPN resistor-equipped transistors;  
R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$

PDTC144W series

#### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | CONDITIONS    | VALUE | UNIT |
|----------------------|---------------------------------------------|---------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | in free air   |       |      |
|                      | SOT54                                       | note 1        | 250   | K/W  |
|                      | SOT23                                       | note 1        | 500   | K/W  |
|                      | SOT346                                      | note 1        | 500   | K/W  |
|                      | SOT323                                      | note 1        | 625   | K/W  |
|                      | SOT490                                      | notes 1 and 2 | 500   | K/W  |
|                      | SOT883                                      | notes 2 and 3 | 500   | K/W  |
|                      | SOT416                                      | note 1        | 833   | K/W  |

#### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

#### CHARACTERISTICS

T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL              | PARAMETER                            | CONDITIONS                                                                  | MIN. | TYP. | MAX. | UNIT       |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------|------|------|------|------------|
| I <sub>CBO</sub>    | collector-base cut-off current       | V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A                                | –    | –    | 100  | nA         |
| I <sub>CEO</sub>    | collector-emitter cut-off current    | V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A                                | –    | –    | 1    | $\mu$ A    |
|                     |                                      | V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C       | –    | –    | 50   | $\mu$ A    |
| I <sub>EBO</sub>    | emitter-base cut-off current         | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A                                 | –    | –    | 110  | $\mu$ A    |
| h <sub>FE</sub>     | DC current gain                      | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA                                | 60   | –    | –    |            |
| V <sub>CEsat</sub>  | collector-emitter saturation voltage | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA                             | –    | –    | 150  | mV         |
| V <sub>i(off)</sub> | input-off voltage                    | I <sub>C</sub> = 100 $\mu$ A; V <sub>CE</sub> = 5 V                         | –    | 1.7  | 1.2  | V          |
| V <sub>i(on)</sub>  | input-on voltage                     | I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 0.3 V                              | 4    | 2.7  | –    | V          |
| R1                  | input resistor                       |                                                                             | 33   | 47   | 61   | k $\Omega$ |
| $\frac{R_2}{R_1}$   | resistor ratio                       |                                                                             | 0.37 | 0.47 | 0.57 |            |
| C <sub>c</sub>      | collector capacitance                | I <sub>E</sub> = I <sub>e</sub> = 0 A; V <sub>CB</sub> = 10 V;<br>f = 1 MHz | –    | –    | 2.5  | pF         |

NPN resistor-equipped transistors;  
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PDTC144W series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT416

Technical drawing of the SOT416 package showing top, bottom, and side views with dimensions D, B, E, A, H<sub>E</sub>, Q, A<sub>1</sub>, c, L<sub>p</sub>, v, w, e, e<sub>1</sub>, b<sub>p</sub>, and detail X.

0 0.5 1 mm  
scale

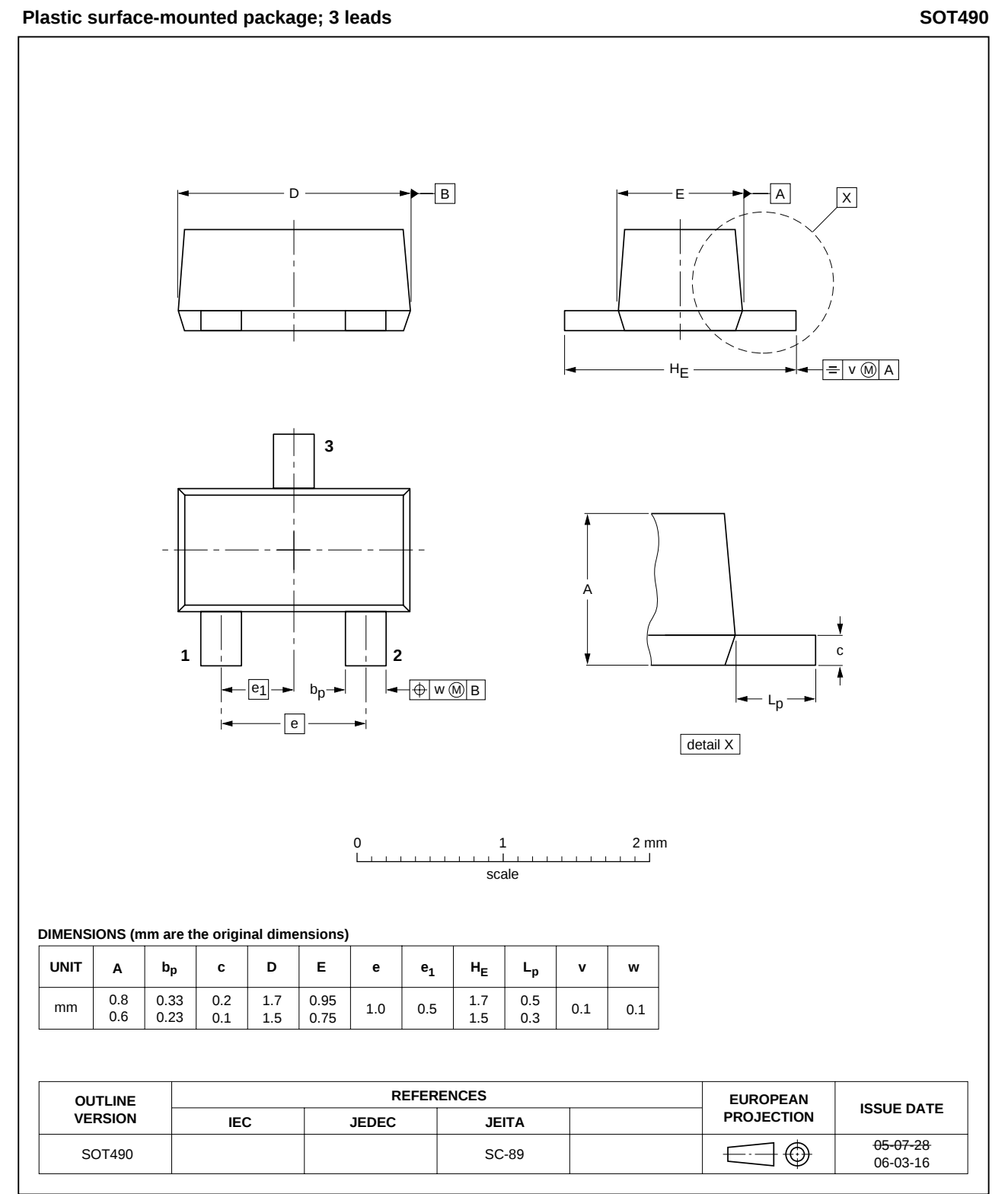
**DIMENSIONS (mm are the original dimensions)**

| UNIT | A            | A <sub>1</sub><br>max | b <sub>p</sub> | c            | D          | E          | e | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | Q            | v   | w   |
|------|--------------|-----------------------|----------------|--------------|------------|------------|---|----------------|----------------|----------------|--------------|-----|-----|
| mm   | 0.95<br>0.60 | 0.1                   | 0.30<br>0.15   | 0.25<br>0.10 | 1.8<br>1.4 | 0.9<br>0.7 | 1 | 0.5            | 1.75<br>1.45   | 0.45<br>0.15   | 0.23<br>0.13 | 0.2 | 0.2 |

| OUTLINE<br>VERSION | REFERENCES |       |       |  | EUROPEAN<br>PROJECTION | ISSUE DATE                      |
|--------------------|------------|-------|-------|--|------------------------|---------------------------------|
|                    | IEC        | JEDEC | JEITA |  |                        |                                 |
| SOT416             |            |       | SC-75 |  |                        | <del>04-11-04</del><br>06-03-16 |

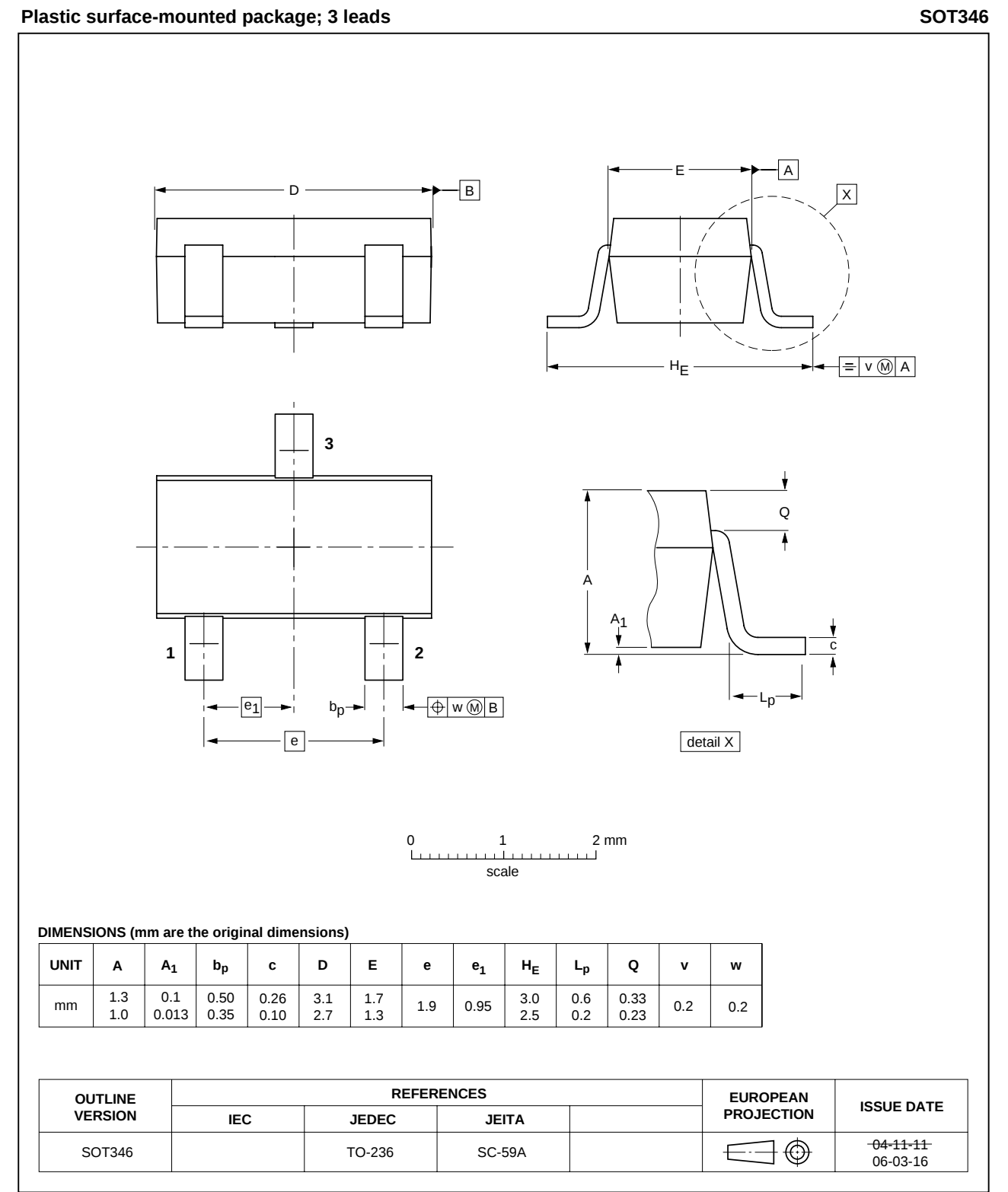
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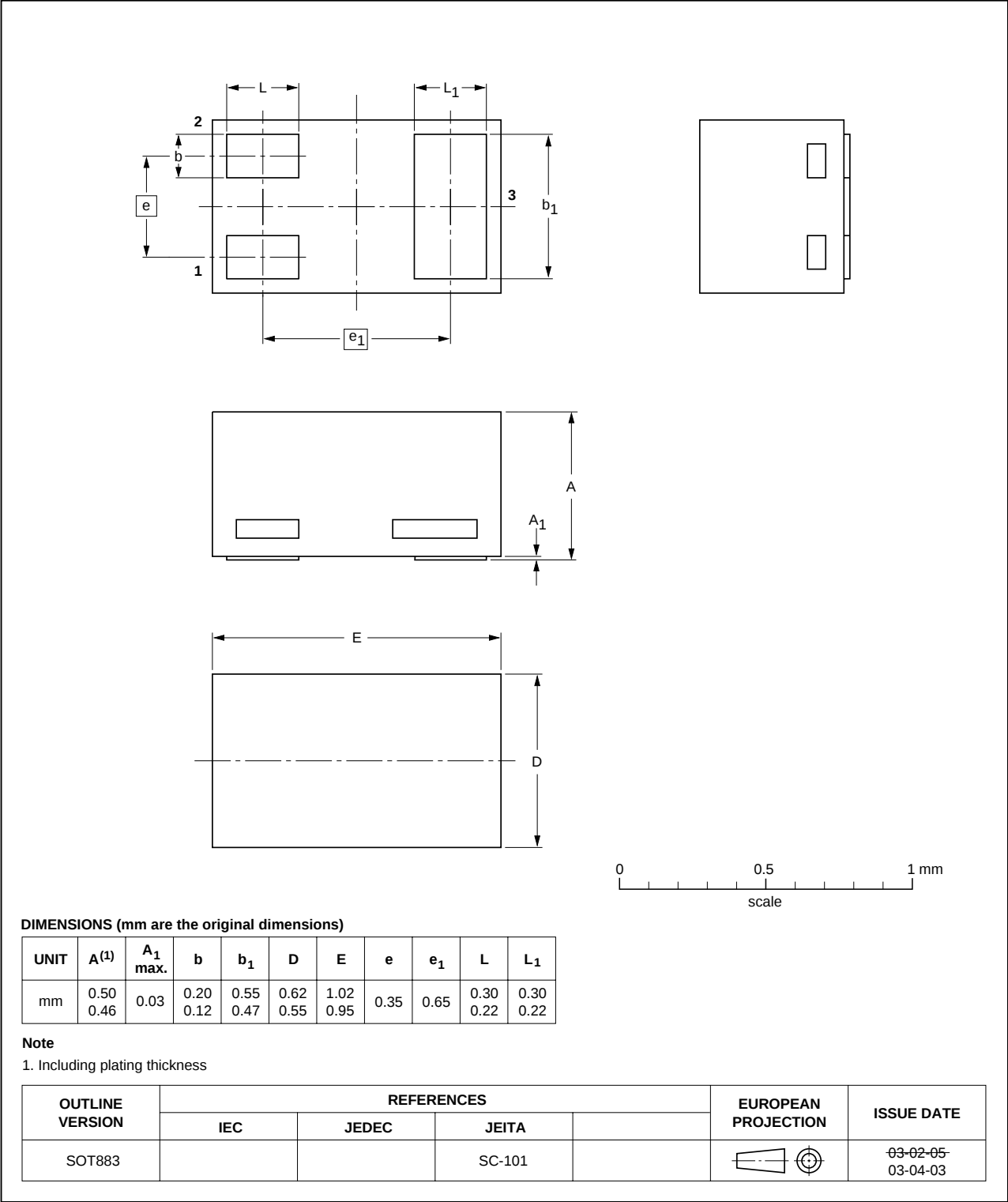


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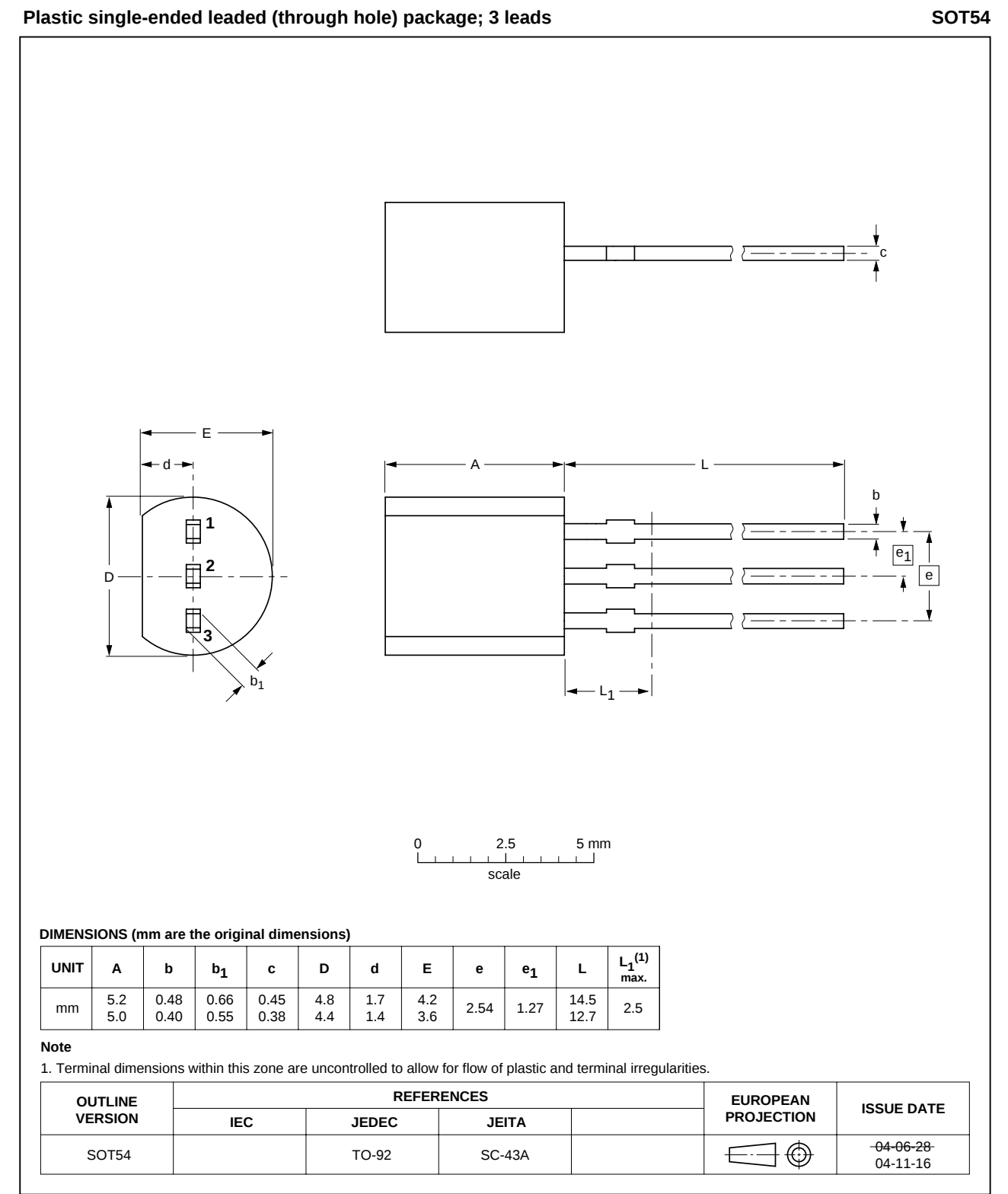
Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



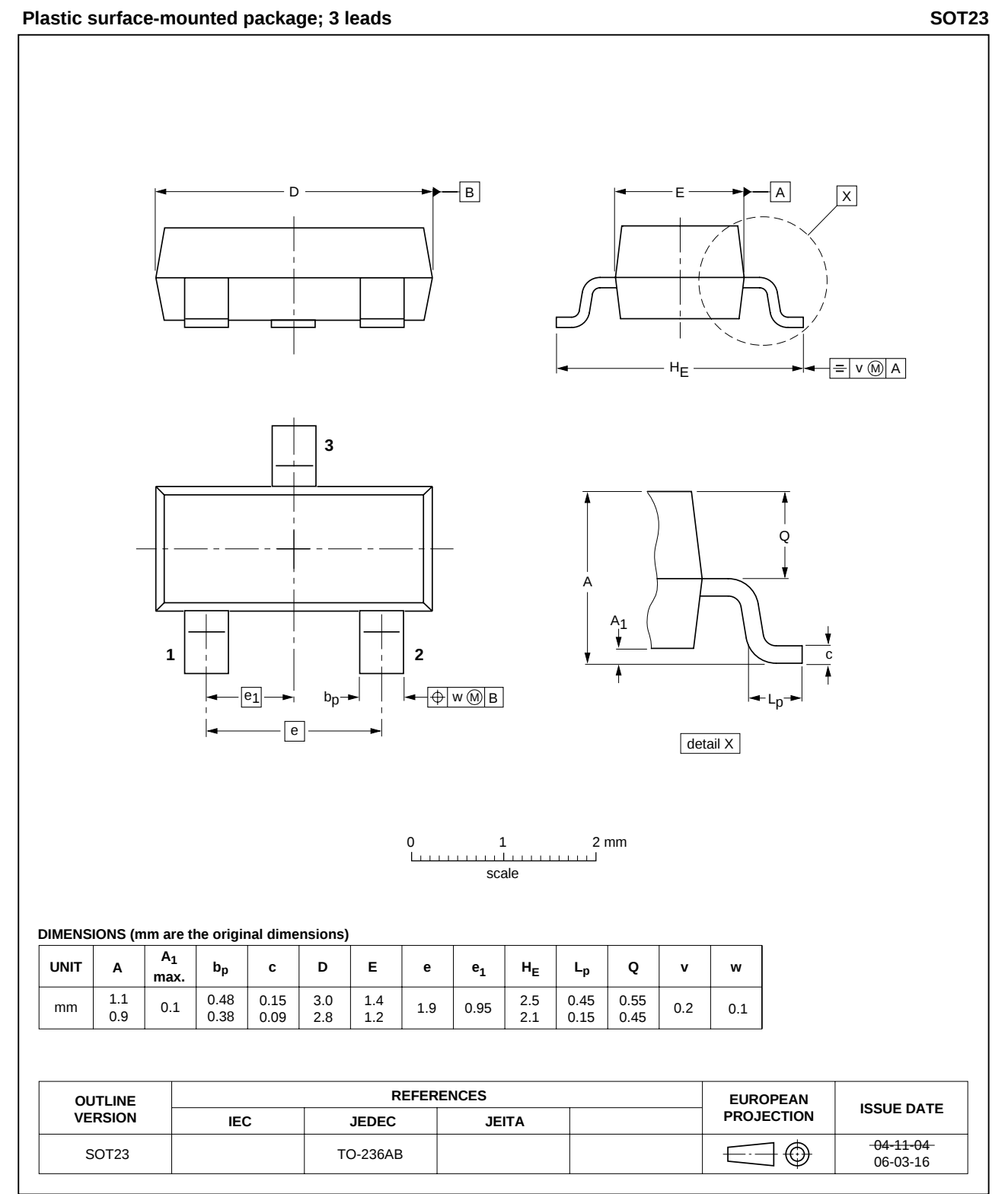
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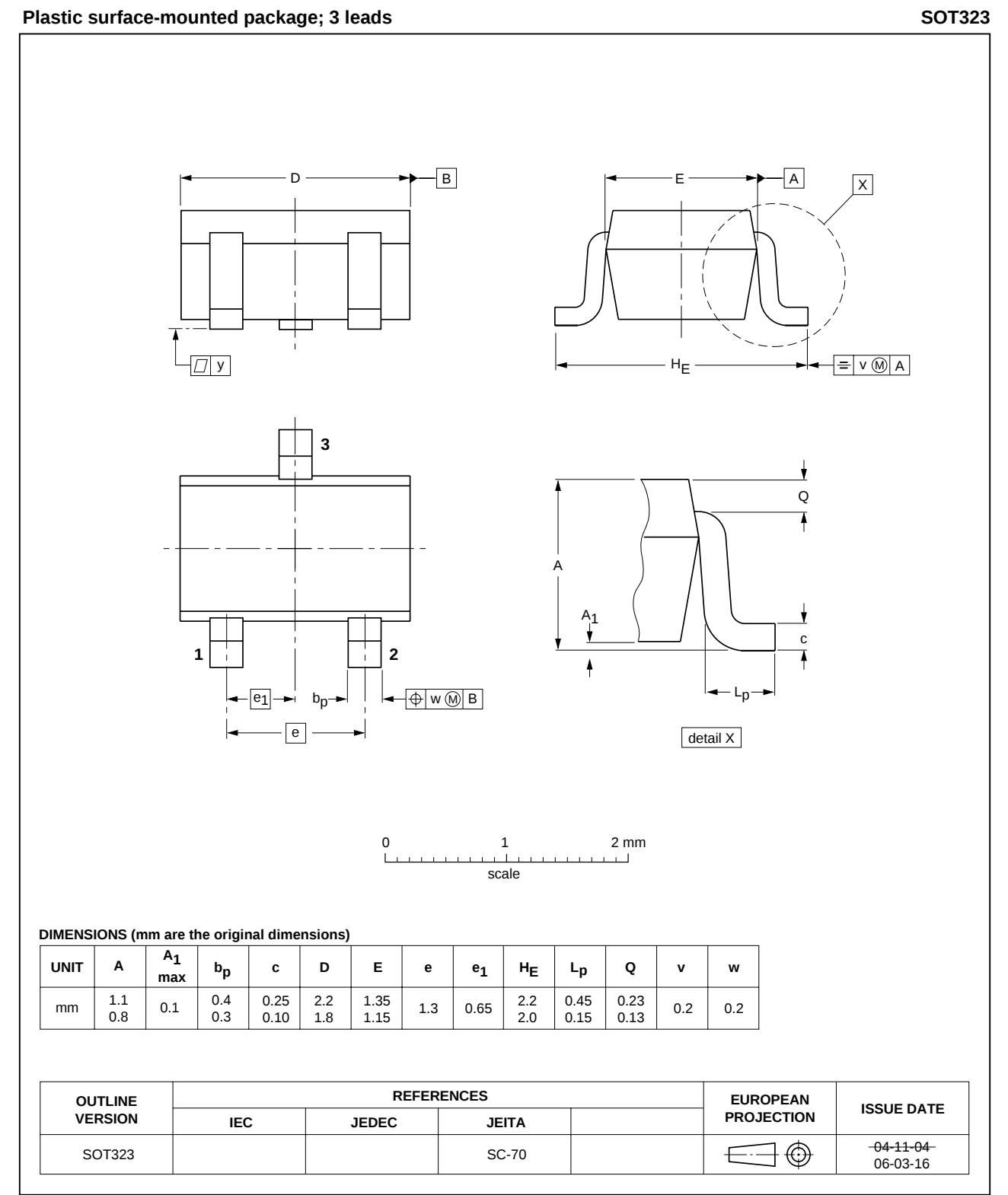
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PDTC144W series



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PDTC144W series



NPN resistor-equipped transistors;  
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PDTC144W series

## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

## Notes

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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Printed in The Netherlands

R75/07/pp14

Date of release: 2004 Aug 17

Document order number: 9397 750 13681

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